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SEMICONDUCTOR®

November 2013

FQPF65N06

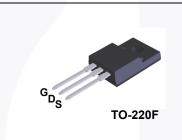
N-Channel QFET[®] MOSFET 60 V, 40 A, 16 m Ω

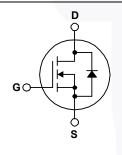
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 40 A, 60 V, $R_{DS(on)}$ = 16 m Ω (Max.) @ V_{GS} = 10 V, I_D = 20 A
- Low Gate Charge (Typ. 48 nC)
- Low Crss (Typ. 100 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQPF65N06	Unit
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous (T _C = 25°	40	А	
	- Continuous (T _C = 100	°C)	28.3	A
I _{DM}	Drain Current - Pulsed	(Note 1)	160	A
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	645	mJ
I _{AR}	Avalanche Current	(Note 1)	40	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.6	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
PD	Power Dissipation $(T_C = 25^{\circ}C)$		56	W
	- Derate above 25°C		0.37	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temperature for Soldering,		300	°C
'L	1/8" from Case for 5 seconds	500	C	

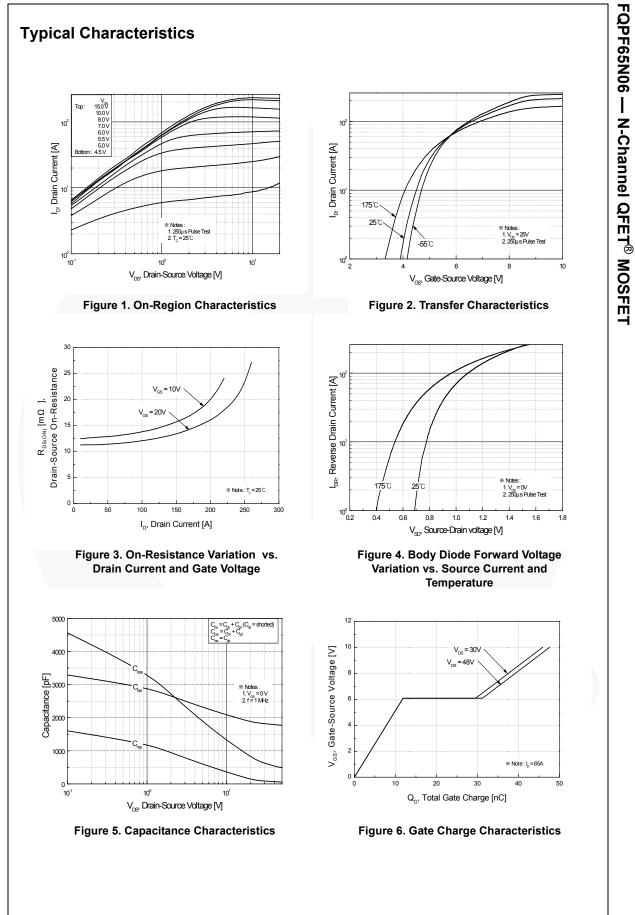
Thermal Characteristics

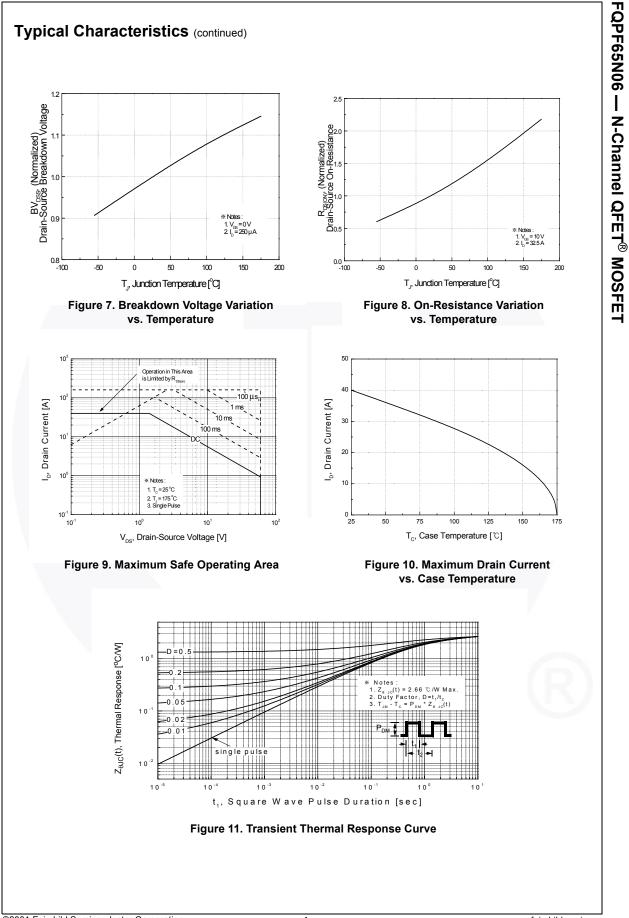
Symbol	Parameter	FQPF65N06	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.66	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

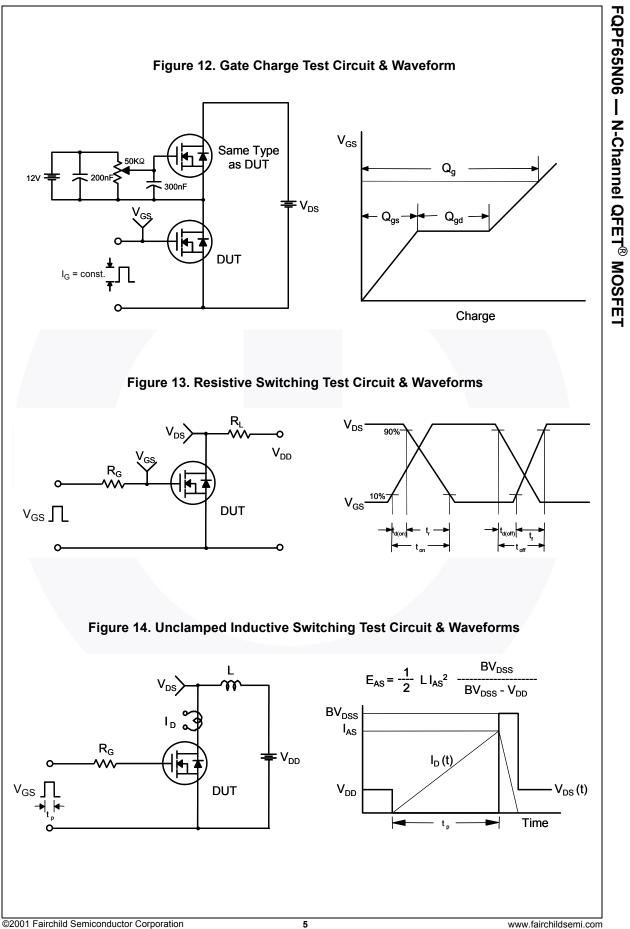
Part NumberTop MarkPackageFQPF65N06FQPF65N06TO-220F		Package	Packing Method Reel		e Tape Width		n Qu	Quantity	
				N/A		50	50 units		
lectri	cal Cl	naracteristics	T _C = 25°C	unless otherwise noted.					
Symbol		Parameter		Test Conditi	ons	Min	Тур	Max	Unit
Off Cha	rootor	iation							
BV _{DSS}		Source Breakdown Vol	200	V _{GS} = 0 V, I _D = 250 µ	Δ	60			V
ΔBV_{DSS} ΔBV_{DSS}	Breakdown Voltage Temperature		0	νgg - ο ν, η - 230 μΑ		00			v
ΔDV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient		I_D = 250 μ A, Referenced to 25°C			0.07		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current		V_{DS} = 60 V, V_{GS} = 0				1	μA	
			V _{DS} = 48 V, T _C = 150°C		1		10	μA	
I _{GSSF}	Gate-E	Body Leakage Current,	Forward	V _{GS} = 25 V, V _{DS} = 0 V		ł		100	nA
I _{GSSR}	Gate-E	Body Leakage Current,	Reverse	V_{GS} = -25 V, V_{DS} = 0	V			-100	nA
On Cha	aracter	istics							
V _{GS(th)}	1	hreshold Voltage	1	V _{DS} = V _{GS} , I _D = 250	uА	2.0		4.0	V
R _{DS(on)}	Static	Static Drain-Source On-Resistance		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$			0.0125	0.016	Ω
9 _{FS}		Forward Transconductance		V _{DS} = 25 V, I _D = 20 A		-	40		S
C _{iss} C _{oss}		Capacitance t Capacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			1850 700	2410 910	pF pF
C _{rss}	Revers	se Transfer Capacitanc	e				100	130	pF
Switch	ina Ch	aracteristics							
		n Delay Time		<u> </u>	- •		20	50	ns
rd(on)		In Rise Time		$V_{DD} = 30 \text{ V}, I_D = 32.5$	ЭΑ,		160	330	ns
()	Turn-C	Off Delay Time		R _G = 25 Ω			90	190	ns
t _r		Off Fall Time			(Note 4)		105	220	ns
t _r d(off)	Turn-C			V _{DS} = 48 V, I _D = 65 A	\		48	65	nC
t _r t _{d(off)} t _f		Bate Charge					12		nC
t _r t _{d(off)} t _f Q _g	Total G	Bate Charge Bource Charge			ι,		14		nC
t _r t _{d(off)} t _f Q _g Q _{gs}	Total G Gate-S			V _{GS} = 10 V	(Note 4)		19.5		
t _r t _{d(off)} t _f Q _g Q _{gs}	Total G Gate-S	Source Charge							
t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd}	Total G Gate-S Gate-I	Source Charge	istics an	V _{GS} = 10 V	(Note 4)				
t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S	Total G Gate-S Gate-I Source	Source Charge Drain Charge		V _{GS} = 10 V d Maximum Rati	(Note 4)				A
t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S	Total G Gate-S Gate-I Source Maxim	Source Charge Drain Charge Diode Character	Source Dio	V _{GS} = 10 V Id Maximum Rati de Forward Current	(Note 4)		19.5		
t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S	Total G Gate-S Gate-I Source Maxim	Source Charge Drain Charge Diode Character um Continuous Drain-S	Source Dio ce Diode Fo	V _{GS} = 10 V Id Maximum Rati de Forward Current	(Note 4)			40	A
t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S I _S V _{SD} t _r	Total G Gate-S Gate-I Source Maxim Maxim Drain-	Source Charge Drain Charge Diode Character um Continuous Drain-Sour	Source Dio ce Diode Fo	V _{GS} = 10 V d Maximum Rati de Forward Current orward Current	(Note 4)		 	40 160	A

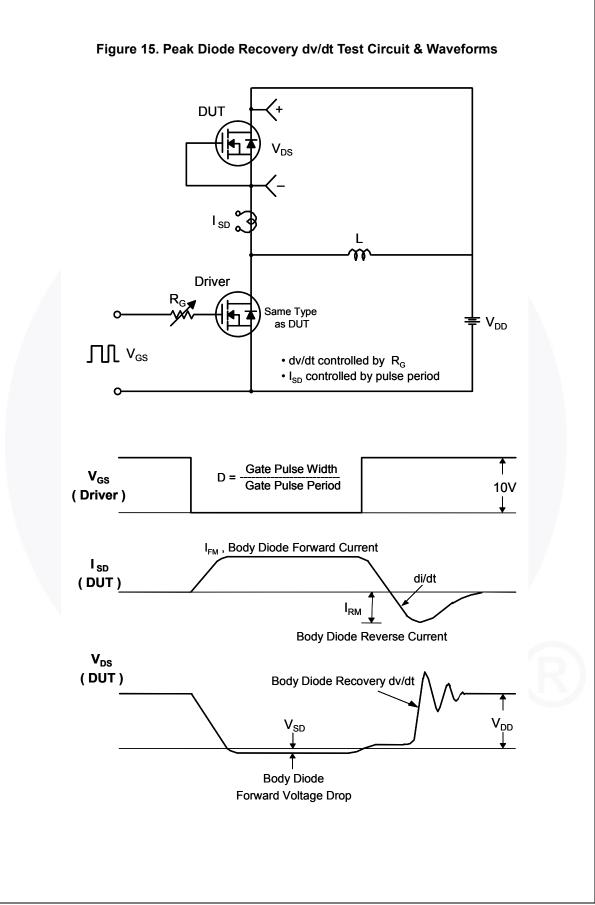
1. Repetitive Rating . Pulse with initiate by maximum junction temperature 2, L = 470 μ H, I_{AS} = 40 A, V_{DD} = 25 V, R_G = 25 Ω, starting T_J = 25°C. 3. I_{SD} = 65 A, di/dt \leq 300 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Essentially Independent of Operating Temperature.

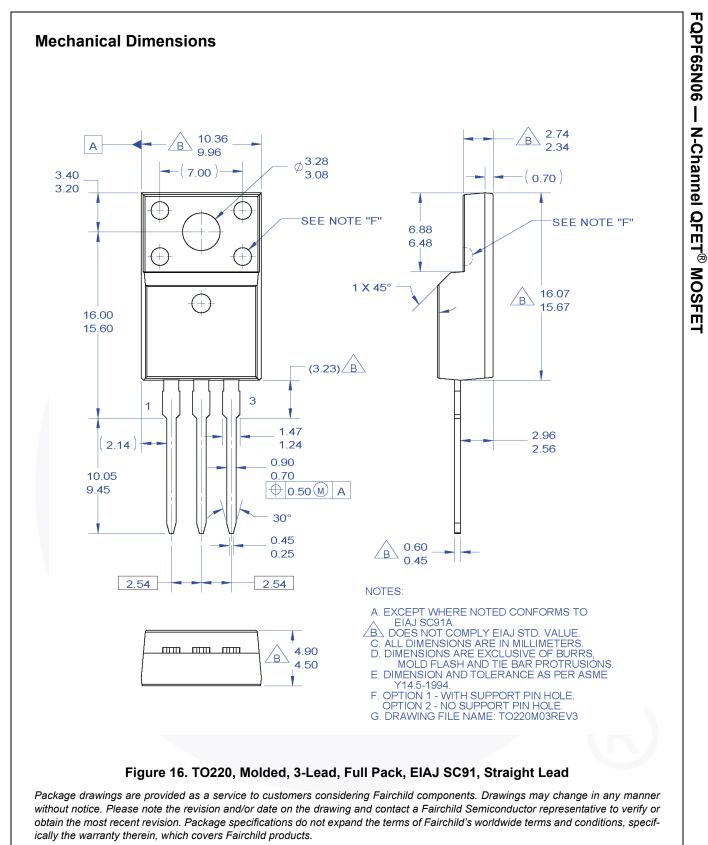
FQPF65N06 — N-Channel QFET[®] MOSFET











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